

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
650V	0.43Ω @ V _{GS} = 10V	14A

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

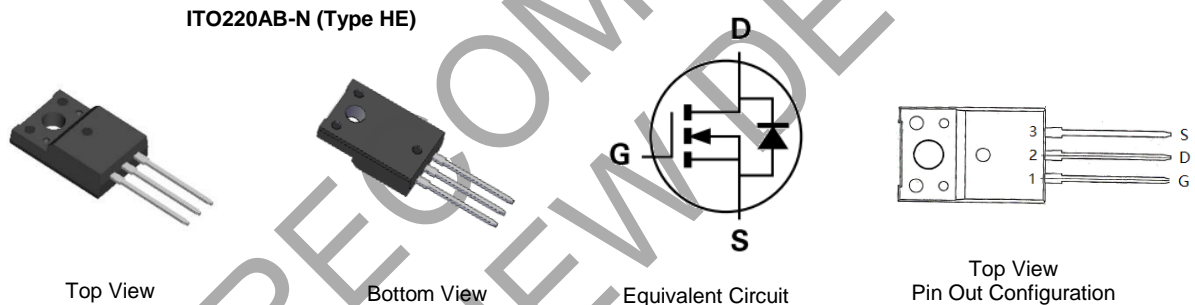
- Motor controls
- Back-lightings
- DC-DC converters
- Power management functions

Features and Benefits

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/ Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: ITO220AB-N
- Package Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Terminal Connections: See Diagram Below
- Weight: 1.9 grams (Approximate)

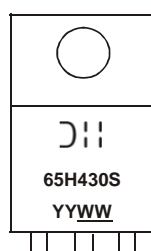


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMJ65H430SCTI	ITO220AB-N (Type HE)	50 Pieces	Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



ITO220AB-N (Type HE)

DII = Manufacturer's Marking
 65H430S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 22 = 2022)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	650	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Continuous Drain Current (Note 5) (Note 9) V _{GS} = 10V	I _D	T _C = +25°C T _C = +100°C	14 9	A
Pulsed Drain Current (Note 5) (Note 9)		I _{DM}	56	A
Continuous Source Current (Note 5) (Note 9)	I _S	14	A	
Pulsed Source Current (Note 5) (Note 9)	I _{SM}	56	A	
Avalanche Current, L = 60mH (Note 6)	I _{AS}	2	A	
Avalanche Energy, L = 60mH (Note 6)	E _{AS}	120	mJ	
Peak Diode Recovery dv/dt (Note 6)	dv/dt	4	V/ns	

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 7) T _A = +25°C T _A = +100°C	P _D	2.5 1	W
Thermal Resistance, Junction to Ambient (Note 7)		R _{θJA}	
Power Dissipation (Note 5) T _C = +25°C T _C = +100°C	P _D	50 20	W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	650	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 650V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±30V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	2	3.7	5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.34	0.43	Ω	V _{GS} = 10V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.86	1.6	V	V _{GS} = 0V, I _S = 10A
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iss}	—	775	—	pF	V _{DS} = 100V, f = 1MHz, V _{GS} = 0V
Output Capacitance	C _{oss}	—	40	—		
Reverse Transfer Capacitance	C _{rss}	—	2.2	—		
Gate Resistance	R _G	—	2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	24.5	—	nC	V _{DD} = 520V, I _D = 5A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	3.8	—		
Gate-Drain Charge	Q _{gd}	—	12.4	—		
Turn-On Delay Time	t _{D(ON)}	—	13	—	ns	V _{DD} = 325V, V _{GS} = 10V, R _G = 4.7Ω, I _D = 5A
Turn-On Rise Time	t _r	—	6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	52	—		
Turn-Off Fall Time	t _f	—	37	—		
Body Diode Reverse Recovery Time	t _{RR}	—	395	—	ns	I _S = 5A, di/dt = 100A/μs,
Body Diode Reverse Recovery Charge	Q _{RR}	—	4.8	—	μC	V _{DD} = 50V

- Notes:
- Device mounted on infinite heatsink.
 - Guaranteed by design. Not subject to production testing.
 - Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
 - Short duration pulse test used to minimize self-heating effect.
 - Limited by maximum junction temperature.

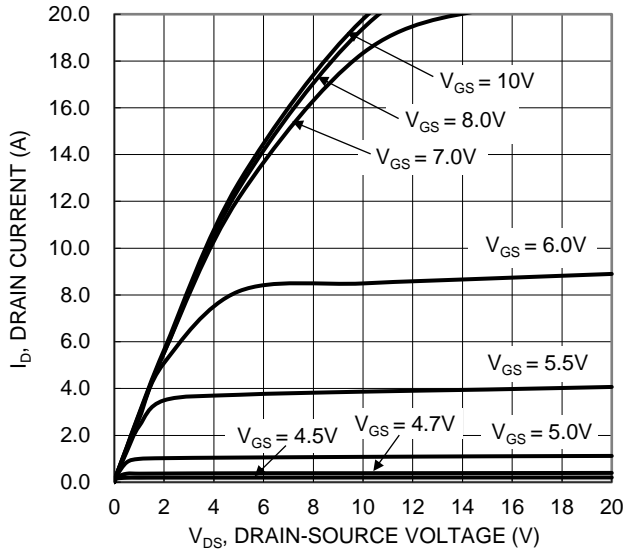


Figure 1. Typical Output Characteristic

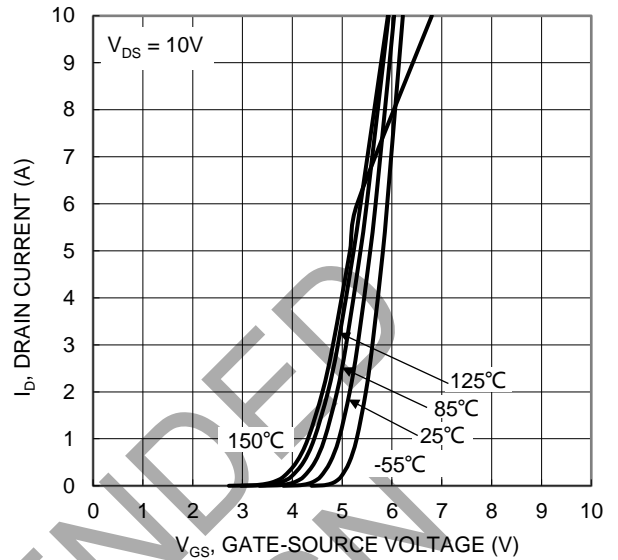


Figure 2. Typical Transfer Characteristic

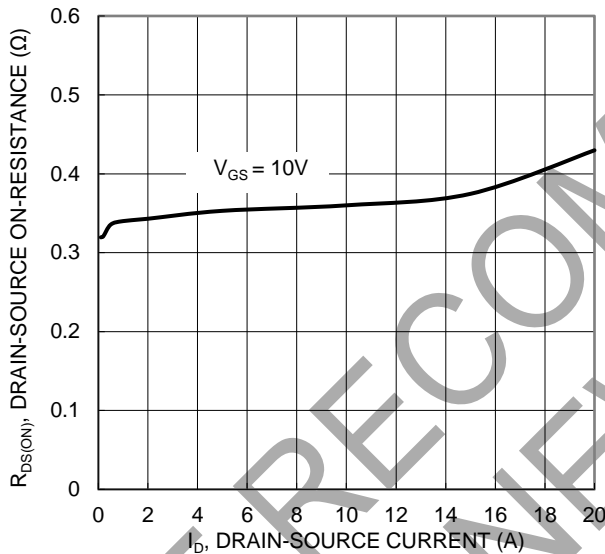


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

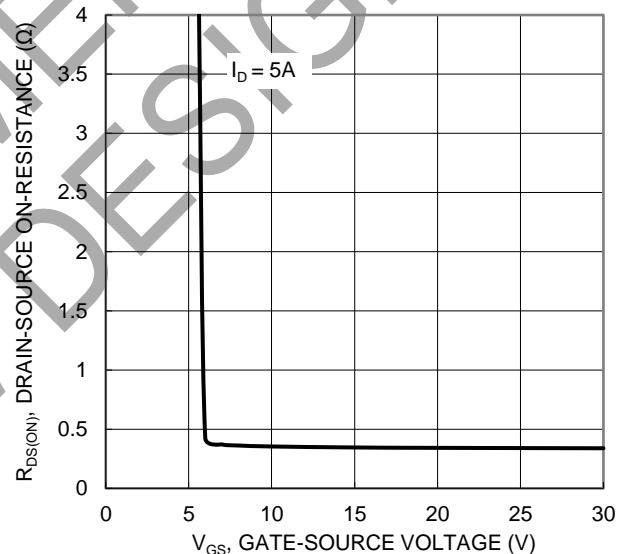


Figure 4. Typical Transfer Characteristic

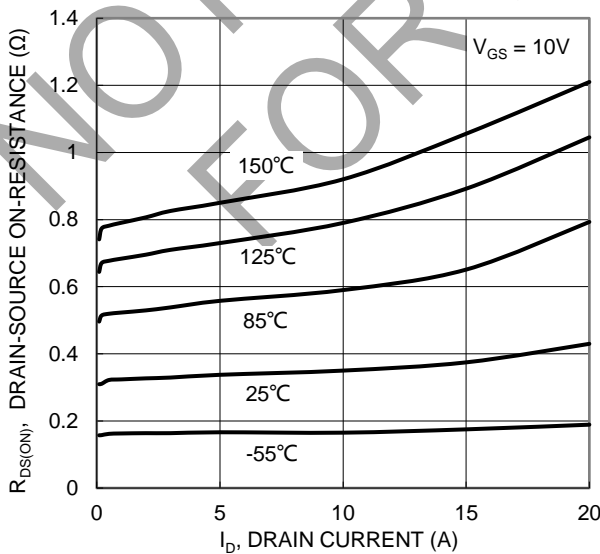


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

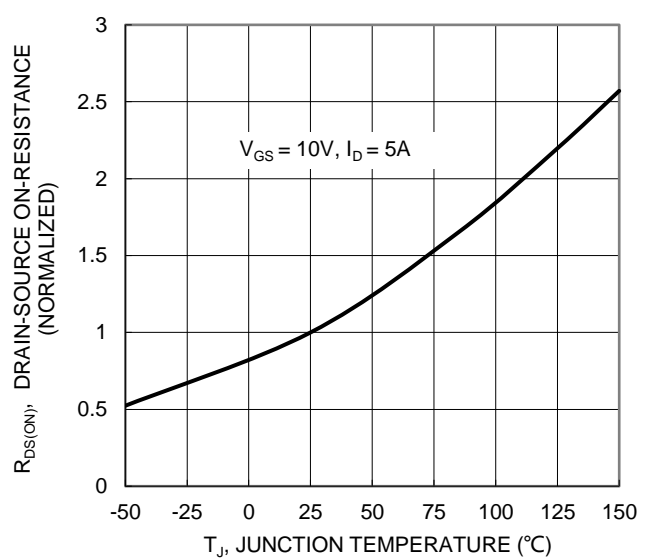


Figure 6. On-Resistance Variation with Junction Temperature

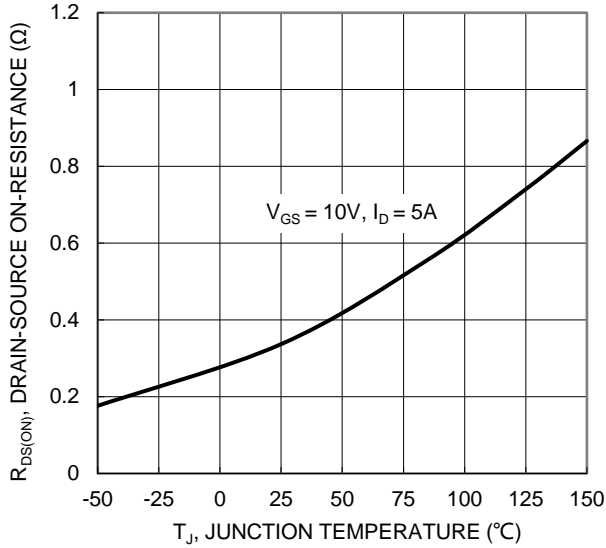


Figure 7. On-Resistance Variation with Junction Temperature

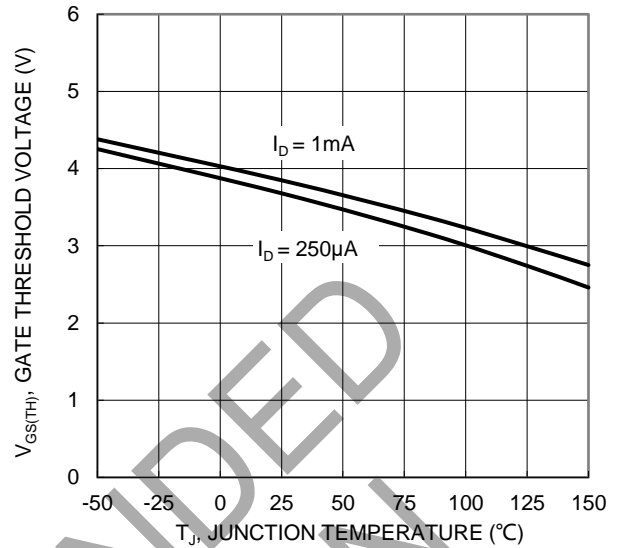


Figure 8. Gate Threshold Variation vs. Junction Temperature

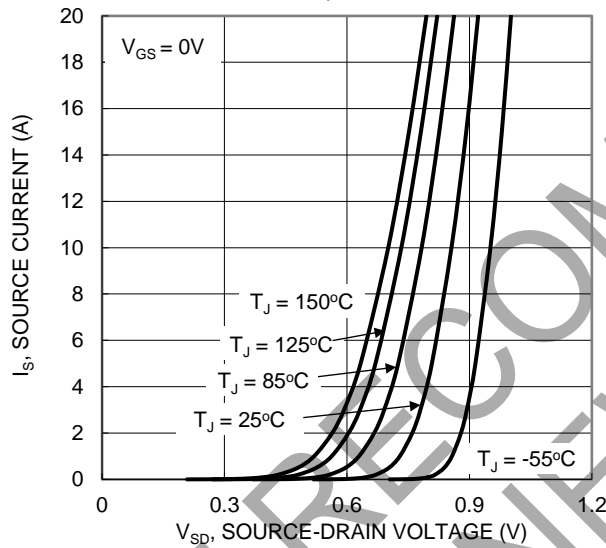


Figure 9. Diode Forward Voltage vs. Current

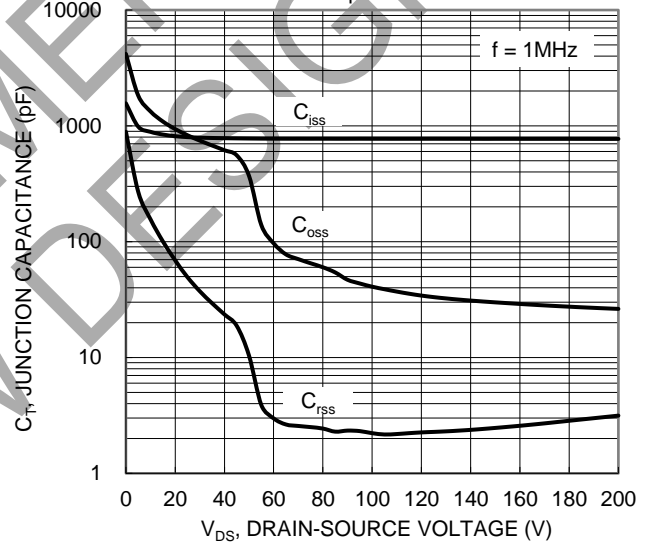


Figure 10. Typical Junction Capacitance

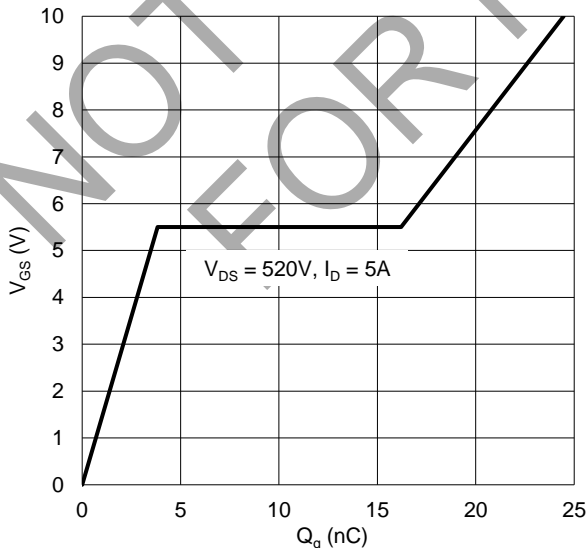


Figure 11. Gate Charge

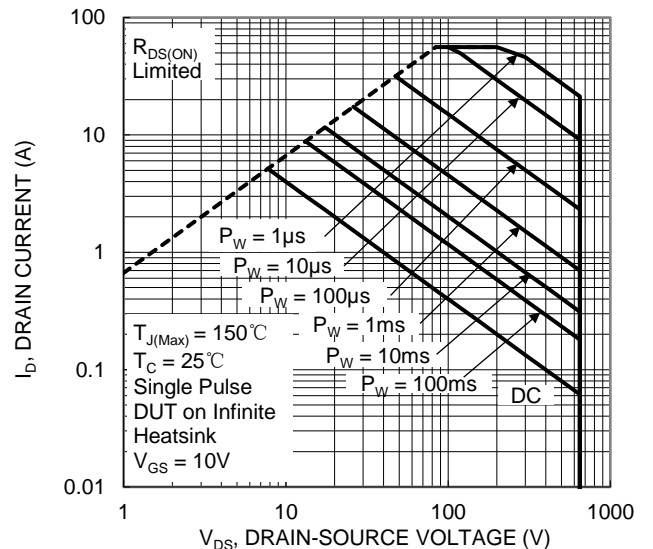


Figure 12. SOA, Safe Operation Area

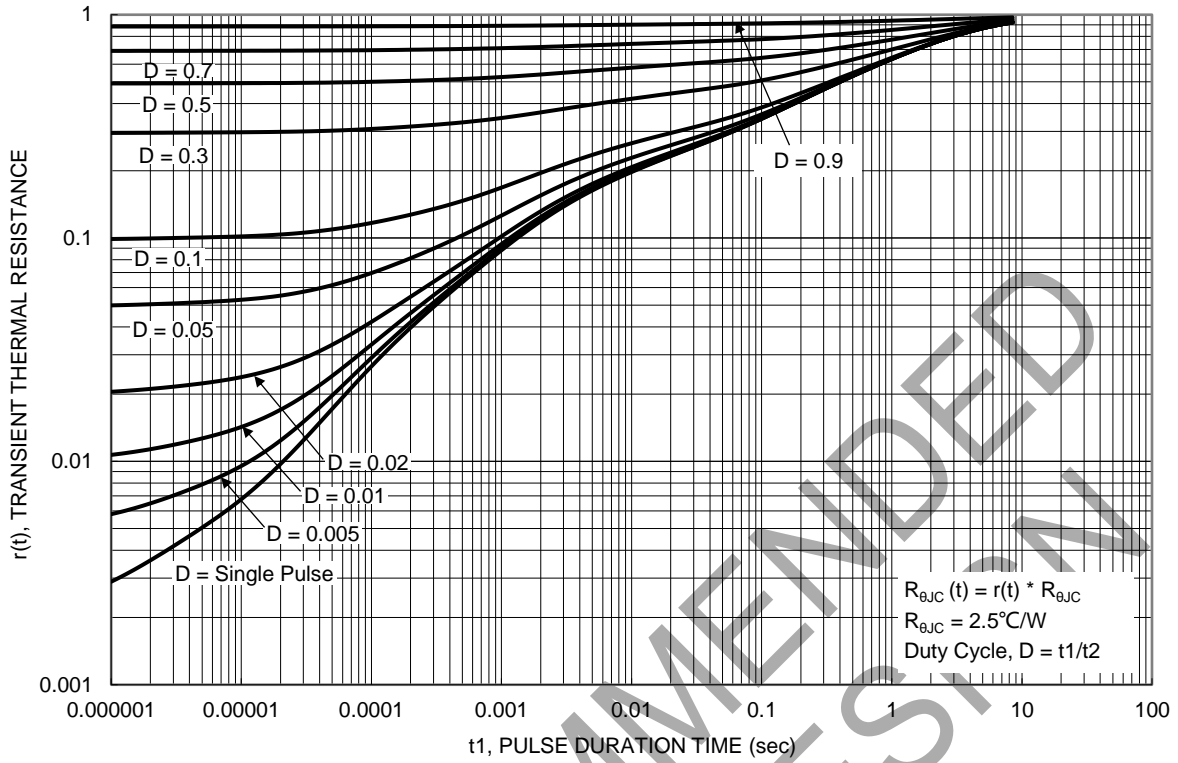


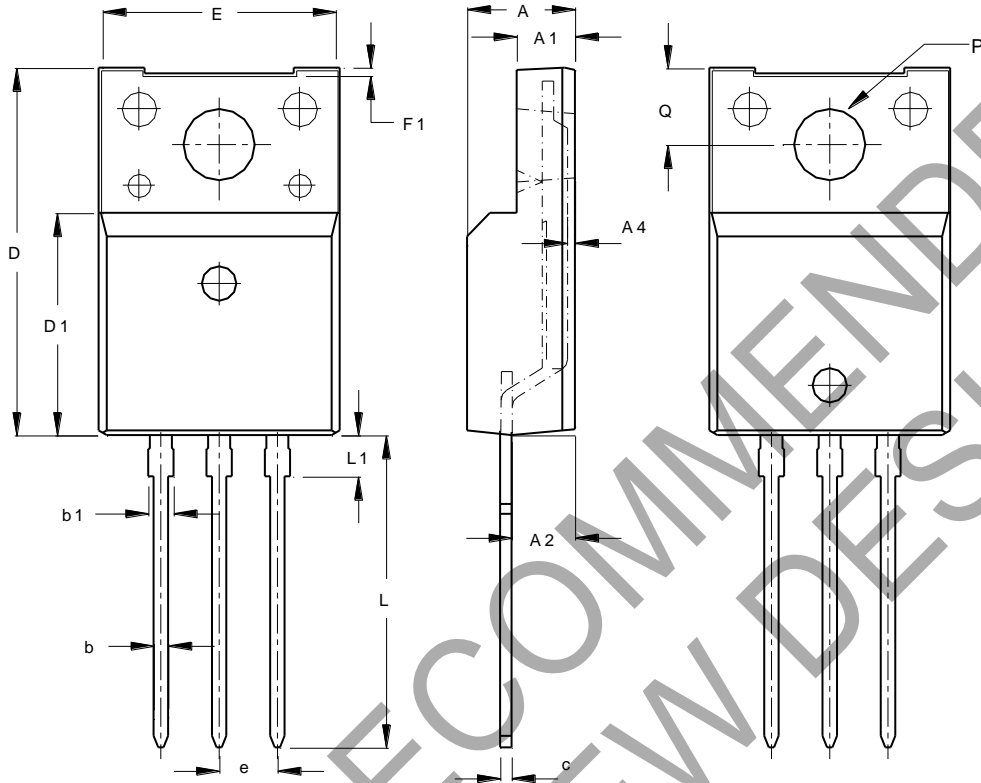
Figure 13. Transient Thermal Resistance

NOT RECOMMENDED FOR NEW DESIGN

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

ITO220AB-N (Type HE)



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Dim	Min	Max	Typ
A	4.60	4.80	4.70
A1	2.60	2.80	2.70
A2	2.47	2.67	2.57
A4	0.30	0.60	0.45
b	0.57	0.69	0.63
b1	1.01	1.15	1.10
c	0.46	0.59	0.50
D	15.90	16.10	16.00
D1	9.58	9.78	9.68
e	2.54 BSC		
E	10.40	10.60	10.50
F1	0.20	0.30	0.25
L	13.45	13.75	13.60
L1	1.70	1.90	1.80
Q	3.25	3.45	3.35
ØP	3.00	3.20	3.10

All Dimensions in mm

NOT RECOMMENDED FOR NEW DESIGNS

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